

UNISONIC TECHNOLOGIES CO., LTD

HER504G **DIODE**

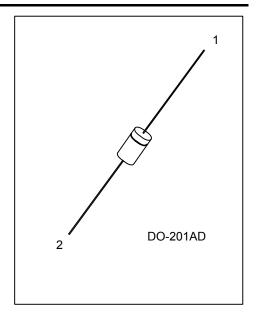
HIGH EFFICIENCY GLASS PASSIVATED RECTIFIERS

DESCRIPTION

The UTC **HER504G** is a high efficiency glass passivated rectifiers, it uses UTC's advanced technology to provide customers with high speed switching, high forward surge current and low reverse leakage, etc.

FEATURES

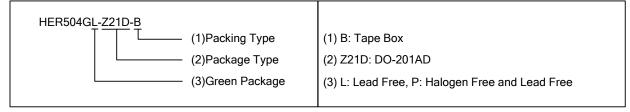
- * High speed switching for high efficiency
- * Low reverse leakage
- * High forward surge current capability



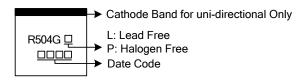
ORDERING INFORMATION

Ordering Number		Dookaga	Pin Assignment		Dooking	
Lead Free	Halogen Free	Package	1	2	Packing	
HER504GL-Z21D-B	HER504GP-Z21D-B	DO-201AD	K	Α	Tape Box	

K: Cathode Note: Pin Assignment: A: Anode



MARKING



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ABSOLUTE MAXIMUM RATINGS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

PARAMETER	SYMBOL	RATINGS	UNIT
Working Peak Reverse Voltage	V_{RWM}	300	V
Repetitive Peak Reverse Voltage	V_{RRM}	300	V
RMS Voltage	V_{RMS}	210	V
DC Blocking Voltage	V_{DC}	300	V
Average Forward Rectified Current 0.375" (9.5mm) Lead Length at T_A =50°C	I _(AV)	5.0	Α
Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load (JEDEC Method)	I _{FSM}	200	А
Junction Temperature	T_J	-65~+150	°C
Storage Temperature	T _{STG}	-65~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient (Note 3)	θ_{JA}	10	°C/W

■ ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Instantaneous Forward Voltage	V_{F}	I _F =5.0A			1.0	V
DC Reverse Current at Rated DC Blocking	I _R	T _A =25°C			10	μΑ
Voltage		T _A =100°C			200	μΑ
Reverse Recovery Time (Note 1)	t _{rr}				50	ns
Junction Capacitance (Note 2)	CJ			75		рF

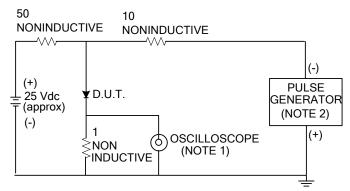
Notes: 1. Reverse recovery condition I_F =0.5A, I_R =1.0A, I_R =0.25A.

- 2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
- 3. Thermal resistance from junction to ambient at 0.375" (9.5mm) lead length, P.C.B. mounted.

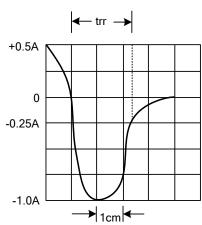
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■ TYPICAL CHARACTERISTICS

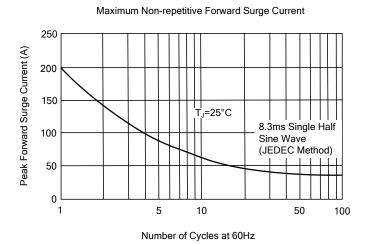
Test Circuit Diagram And Reverse Recovery Time Characteristics

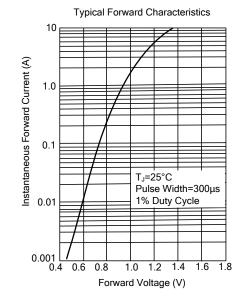


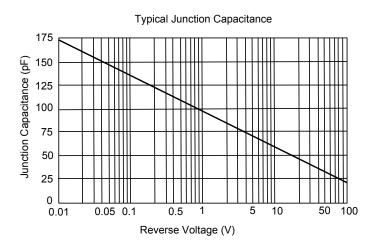
Notes: 1. Rise Time=7ns max. Input Impedance=1 megohm 22pF 2. Rise Time=10ns max. Source Impedance= 50 ohms

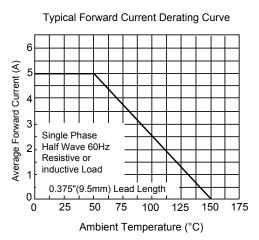


SET TIME BASE FOR 50/10ns/cm









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